LM185-1.2, LM285-1.2, LM385-1.2, LM385B-1.2, LM385Y-1.2 MICROPOWER VOLTAGE REFERENCES

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Operating Current Range
 LM185...10 μA to 20 mA

– LM285 . . . 10 μA to 20 mA

LM385 . . . 15 μA to 20 mA
 LM385B . . . 15 μA to 20 mA

• 1% and 2% Initial Voltage Tolerance

Reference Impedance

- LM185 . . . 0.6 Ω Max at 25°C

- LM385 . . . 1 Ω Max at 25°C

- All Devices . . . 1.5 Ω Max Over Full

- Temperature Range

Very Low Power Consumption

• Applications:

- Portable Meter References

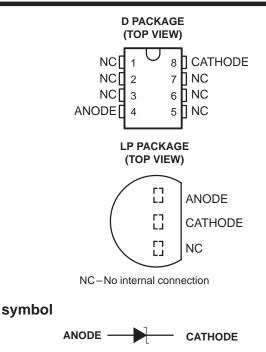
Portable Test Instruments

Battery-Operated Systems

Current-Loop Instrumentation

- Panel Meters

 Designed to be Interchangeable With National LM185-1.2, LM285-1.2, and LM385-1.2



description

These micropower two-terminal band-gap voltage references operate over a 10-µA to 20-mA current range and feature exceptionally low dynamic impedance and good temperature stability. On-chip trimming provides tight voltage tolerance. The LM185-1.2 series band-gap reference has low noise and long-term stability.

The LM185-1.2 series design makes the devices exceptionally tolerant of capacitive loading and thus easier to use in most reference applications. The wide dynamic operating temperature range accommodates varying current supplies with excellent regulation.

The extremely low-power drain of the LM185-1.2 series makes them useful for micropower circuitry. These voltage references can be used to make portable meters, regulators, or general-purpose analog circuitry with battery life approaching shelf life. The wide operating current range allows them to replace older references with tighter-tolerance parts.

The LM185-1.2 is characterized for operation over the full military temperature range of -55° C to 125°C. The LM285-1.2 is characterized for operation from -40° C to 85°C. The LM385-1.2 and LM385B-1.2 are characterized for operation from 0°C to 70°C.

AVAILABLE OPTIONS

	V-	PACKAGED D	CHIP FORM		
TA	V _Z TOLERANCE	SMALL OUTLINE (D)	PLASTIC (LP)	(Y)	
0°C to 70°C	2%	LM385D-1.2	LM385LP-1.2		
0 0 10 70 0	1%	LM385BD-1.2	LM385BLP-1.2	LM385Y-1.2	
-40°C to 85°C	1%	LM285D-1.2	LM285LP-1.2	LIVI3031-1.2	
-55°C to 125°C	1%	LM185D-1.2	LM185LP-1.2		

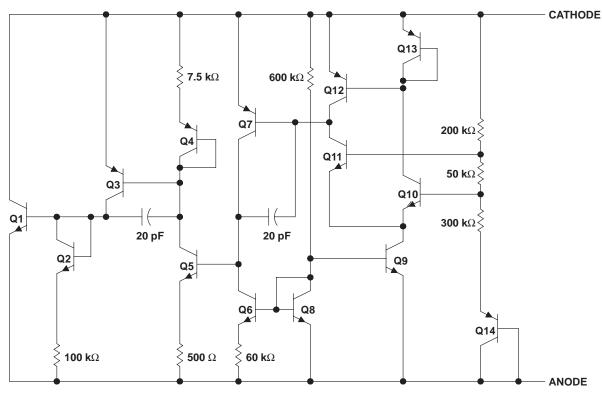
[†] For ordering purposes, the decimal point in the part number must be replaced with a hyphen (i.e., show the -1.2 suffix as "-1-2").

The D package is available taped and reeled. Add the suffix R to the device type (e.g., LM385DR-1-2). The chip form is tested at $T_A = 25^{\circ}C$.



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schematic



NOTE A: Component values shown are nominal.

absolute maximum ratings over operating free-air temperature range†

Reverse current, I _R	30 mA
Forward current, I _F	10 mA
Operating free-air temperature range, T _A : LM185-1.2	. −55°C to 125°C
LM285-1.2	−40°C to 85°C
LM385-1.2, LM385B-1.2	0°C to 70°C
Storage temperature range, T _{stg}	. −65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

recommended operating conditions

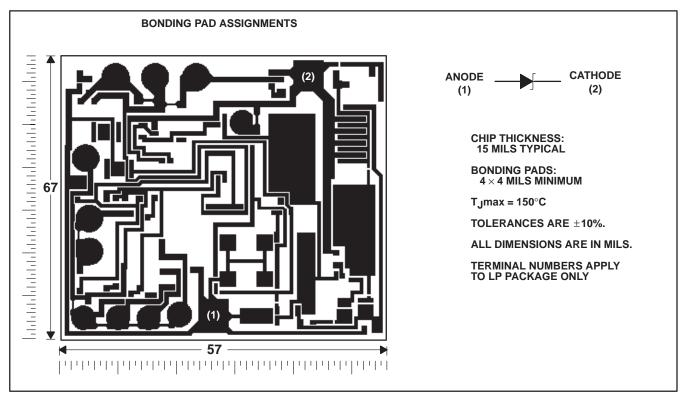
			MAX	UNIT
Reference current, IZ				mA
	LM185-1.2	-55	125	
Operating free-air temperature range, TA	LM285-1.2	-40	85	°C
	LM385-1.2, LM385B-1.2	0	70	



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LM385Y-1.2 chip information

This chip, when properly assembled, displays characteristics similar to the LM385-1.2 (see electrical tables). Thermal compression or ultrasonic bonding can be used on the doped aluminum bonding pads. The chip can be mounted with conductive epoxy or a gold-silicon preform.



electrical characteristics at specified free-air temperature

PARAMETER		TEST CONDITIONS	T _A †	LM185-1.2 LM285-1.2		LM385-1.2		LM385B-1.2			UNIT		
				MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
٧z	Reference voltage	$I_Z = I \min to 20 \text{ mA}^{\ddagger}$	25°C	1.223	1.235	1.247	1.21	1.235	1.26	1.223	1.235	1.247	V
ανΖ	Average temperature coefficient of reference voltage§	$I_Z = I \min to 20 \text{ mA}^{\ddagger}$	25°C		±20			±20			±20		ppm/°C
	Change in reference voltage with current	$I_Z = I \text{ min to 1 mA}^{\ddagger}$	25°C			1			1			1	
ΔVZ			Full range			1.5			1.5			1.5	mV
		$I_Z = 1 \text{ mA to } 20 \text{ mA}$	25°C			12			20			20	
			Full range			30			30			30	
$\Delta V_{Z}/\Delta t$	Long-term change in reference voltage	ΙΖ = 100 μΑ	25°C		±20			±20			±20		ppm/khr
Izmin	Minimum reference current		Full range		8	10		8	15		8	15	μΑ
z _Z	Reference impedance	I _Z = 100 μA, f = 25 Hz	25°C		0.2	0.6		0.4	1		0.4	1	Ω
			Full range			1.5			1.5			1.5	
Vn	Broadband noise voltage	$I_Z = 100 \mu A$, f = 10 Hz to 10 kHz	25°C		60	·		60			60		μV

MICROPOWER VOLTAGE REFERENCES

LM185-1.2, LM285-1.2, LM385-1.2, LM385B-1.2, LM385Y-1.2

† Full range is -55°C to 125°C for the LM185-1.2, -40°C to 85°C for the LM285-1.2, and 0°C to 70°C for the LM385-1.2 and LM385B-1.2.
‡ I min = 10 µA for the LM185-1.2 and LM285-1.2. I_{min} = 15 µA for the LM385-1.2 and LM385B-1.2.
§ The average temperature coefficient of reference voltage is defined as the total change in reference voltage divided by the specified temperature range.

LM185-1.2, LM285-1.2, LM385-1.2, LM385B-1.2, LM385Y-1.2 MICROPOWER VOLTAGE REFERENCES

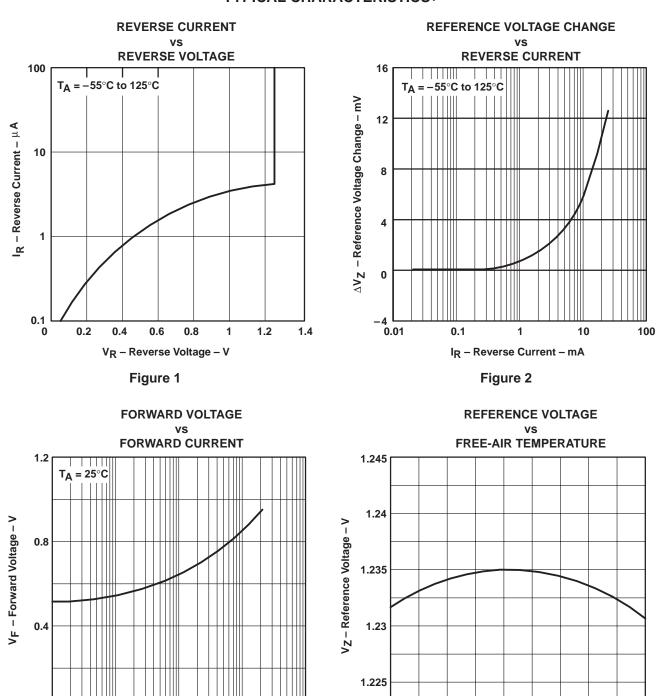
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electrical characteristics, $T_A = 25^{\circ}C$

PARAMETER		TEST CONDITIONS	LI	UNIT		
		TEST CONDITIONS	MIN	TYP	MAX	UNII
٧z	Reference voltage	$I_Z = 15 \mu\text{A} \text{ to } 20 \text{mA}$	1.21	1.235	1.26	V
αΛΣ	Average temperature coefficient of reference voltage†	$I_Z = 15 \mu\text{A} \text{ to } 20 \text{mA}$		±20		ppm/°C
ΔVZ	Change in reference valtage with gurrent	$I_Z = 15 \mu A \text{ to 1 mA}$	A to 1 mA		1	m)/
	Change in reference voltage with current	$I_Z = 1 \text{ mA to } 20 \text{ mA}$			20	mV
$\Delta V_{Z}/\Delta t$	Long-term change in reference voltage	ΙΖ = 100 μΑ		±20		ppm/khr
IZmin	Minimum reference current			8	15	μΑ
z _Z	Reference impedance	I _Z = 100 μA		0.4	1	Ω
v _n	Broadband noise voltage	$I_Z = 100 \mu A$, f = 10 Hz to 10 kHz		60		μV

[†] The average temperature coefficient of reference voltage is defined as the total change in reference voltage divided by the specified temperature range.

TYPICAL CHARACTERISTICS[†]



100

10

IF - Forward Current - mA

Figure 3



1.220

-55 -35

25

Figure 4

 T_A – Free-Air Temperature – $^{\circ}C$

45

65

85

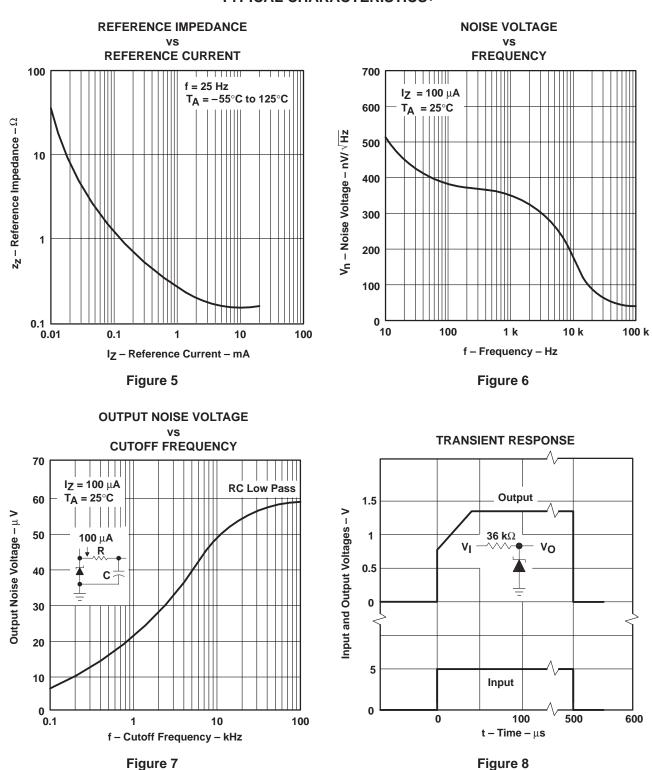
105 125

0.01

0.1

[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

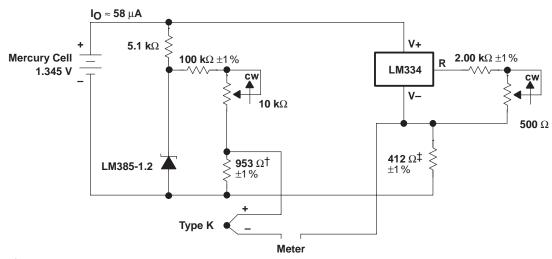
TYPICAL CHARACTERISTICS[†]



[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.



APPLICATION INFORMATION



[†] Adjust for 11.15 mV at 25°C across 953 Ω

Figure 9. Thermocouple Cold-Junction Compensator

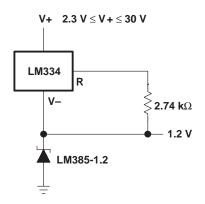


Figure 10. Operation Over a Wide Supply Range

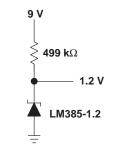


Figure 11. Reference From a 9-V Battery

 $[\]ddagger$ Adjust for 12.17 mV at 25°C across 412 Ω

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